

### **General Description**

The WSR80N10 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSR80N10 meet the RoHS and Green Product requirement,100% EAS guaranteed with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

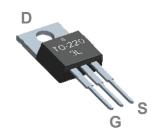
### **Product Summery**

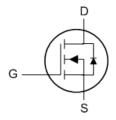
BV <sub>DSS</sub>	R <sub>DSON</sub>	I <sub>D</sub>
100V	10mΩ	85A

### **Applications**

- Power Management in TV Converter.
- DC-DC Converter
- LED TV Back Light

### **TO-220AB Pin Configuration**





### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	±25	V
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	85	Α
I <sub>D</sub> @T <sub>C</sub> =100℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	65	Α
I <sub>D</sub> @T <sub>A</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	10	Α
I <sub>D</sub> @T <sub>A</sub> =70 °C Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>		8.2	Α
I <sub>DM</sub>	Pulsed Drain Current <sup>2,</sup> T <sub>C</sub> =25°C	200	Α
EAS	Avalanche Energy, Single pulse,L=0.5mH	189	mJ
I <sub>AS</sub>	Avalanche Current, Single pulse,L=0.5mH	28	Α
P <sub>D</sub> @T <sub>C</sub> =25℃	Total Power Dissipation⁴	150	W
P <sub>D</sub> @T <sub>C</sub> =100°C Total Power Dissipation <sup>4</sup>		75	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	$^{\circ}$
$T_J$	Operating Junction Temperature Range	150	$^{\circ}$

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
$R_{ heta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>		50	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case <sup>1</sup>		1.1	°C/W



### Electrical Characteristics (T<sub>J</sub>=25 C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV <sub>DSS</sub>	BV <sub>DSS</sub> Drain-Source Breakdown Voltage V <sub>GS</sub> =0V , I <sub>D</sub> =250uA		100			V	
$\triangle BV_{DSS}/\triangle T_{J}$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.096		V/°C	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =30A		10	13	mΩ	
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> . In =250uA	2.0	3.0	4.0	٧	
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	VGS-VDS , ID -250UA		-5.5		mV/℃	
	Drain Source Leakage Current	$V_{DS}$ =80V , $V_{GS}$ =0V , $T_{J}$ =25 $^{\circ}$ C			1		
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{DS}$ =80V , $V_{GS}$ =0V , $T_{J}$ =55 $^{\circ}$ C			5	- uA	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm 20V$ , $V_{DS}$ = $0V$			±100	nA	
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =30A		27		S	
$R_g$	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		1.0	1.8	Ω	
$Q_g$	Total Gate Charge (10V)			42			
$Q_{gs}$	Gate-Source Charge	V <sub>DS</sub> =80V , V <sub>GS</sub> =10V , I <sub>D</sub> =30A		12		nC	
$Q_{gd}$	Gate-Drain Charge			12			
T <sub>d(on)</sub>	Turn-On Delay Time			19			
Tr	Rise Time	$V_{DD}$ =50V , $V_{GS}$ =10V , $R_{G}$ =3 $\Omega$ ,		9			
T <sub>d(off)</sub>	Turn-Off Delay Time	I <sub>D</sub> =1A		36		ns	
T <sub>f</sub>	Fall Time			22			
C <sub>iss</sub>	Input Capacitance			2100			
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		255		pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			100			

### **Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	V <sub>DD</sub> =25V , L=0.5mH , I <sub>AS</sub> =28A	160			mJ

### **Diode Characteristics**

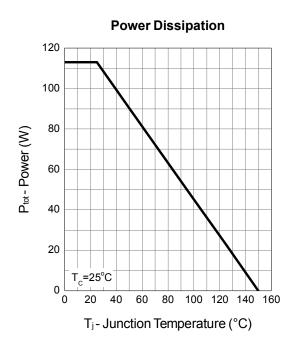
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,6</sup>	V =V =0V Force Current			35	Α
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			60	Α
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =15A , T <sub>J</sub> =25℃			1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I= 454 di/db 4004/ T 05°C		42		nS
Qrr	Reverse Recovery Charge	IF=15A,dI/dt=100A/µs,T <sub>J</sub> =25℃		90		nC

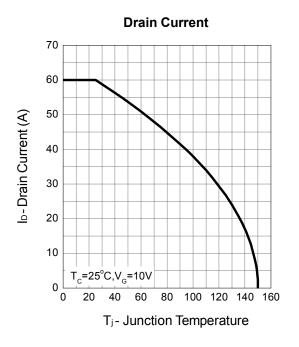
#### Note:

- 1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, t<10 sec.
- 2.The data tested by pulsed , pulse width  $\,\leq\,300\text{us}$  , duty cycle  $\,\leq\,2\%$
- 3. The EAS data shows Max. rating . The test condition is  $V_{DS}$ =25V, $V_{GS}$ =10V,L=0.5mH,I<sub>AS</sub>=26A
- 4.The power dissipation is limited by 150  $^{\circ}\mathrm{C}\,$  junction temperature
- 5. The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

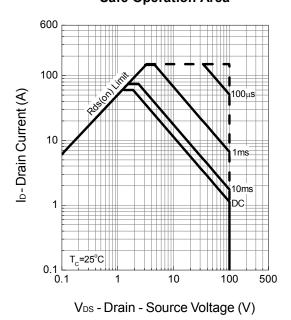


### **Typical Operating Characteristics**

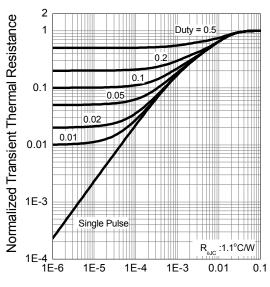




### **Safe Operation Area**



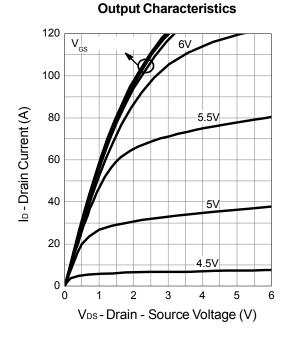
### **Thermal Transient Impedance**



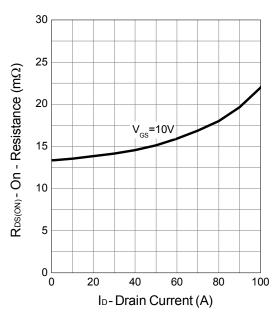
Square Wave Pulse Duration (sec)



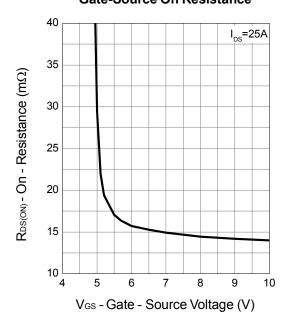
### **Typical Operating Characteristics (Cont.)**



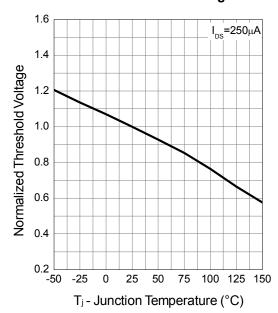
#### **Drain-Source On Resistance**



### **Gate-Source On Resistance**



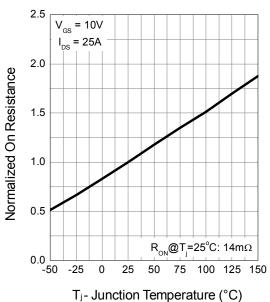
### **Gate Threshold Voltage**



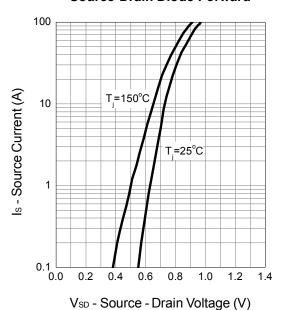


### **Typical Operating Characteristics (Cont.)**

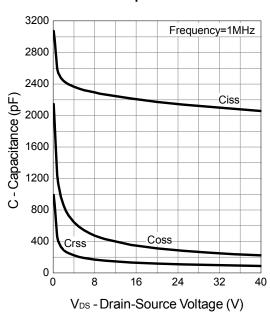
# **Drain-Source On Resistance**



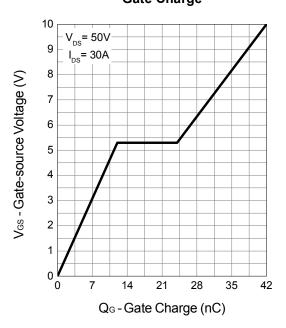
#### Source-Drain Diode Forward



#### Capacitance

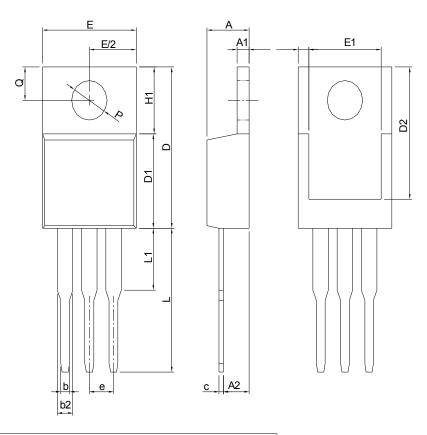


### **Gate Charge**



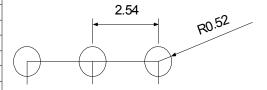


## Package Information TO-220AB



Ş	TO-220				
SYMBO	MILLIMI	ETERS	INC	HES	
5	MIN.	MAX.	MIN.	MAX.	
Α	3.56	4.83	0.140	0.190	
A1	0.51	1.40	0.020	0.055	
A2	2.03	2.92	0.080	0.115	
b	0.38	1.02	0.015	0.040	
b2	1.14	1.78	0.045	0.070	
С	0.36	0.61	0.014	0.024	
D	14.22	16.51	0.560	0.650	
D1	8.38	9.02	0.330	0.355	
D2	12.19	13.65	0.480	0.537	
Е	9.65	10.67	0.380	0.420	
E1	6.86	8.89	0.270	0.350	
е	2.54	BSC	0.100	) BSC	
H1	5.84	6.86	0.230	0.270	
L	12.70	14.73	0.500	0.580	
L1		6.35		0.250	
Р	3.53	4.09	0.139	0.161	
Q	2.54	3.43	0.100	0.135	

### RECOMMENDED LAND PATTERN



UNIT: mm



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